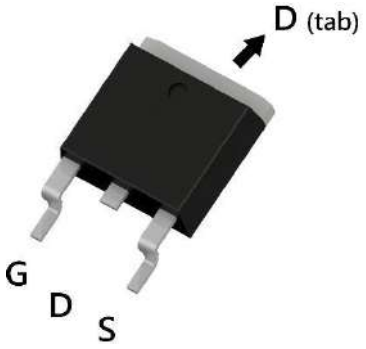
N-Channel Enhancement Mode Power MOSFET

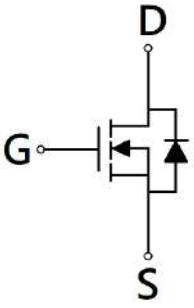
Features:

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic

TO-263



BV_{DSS}	100V
I_D@V_{GS}=10V, T_C=25°C	120A
I_D@V_{GS}=10V, T_A=25°C	24A
$R_{DS(ON)}$ typ. @V_{GS}=10V, I_D=20A	3.2mΩ



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KUE3D0N10R	TO-263 (Pb-free lead plating and RoHS compliant package)	800 pcs / Tape & Reel

Absolute Maximum Ratings (T_A=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current @ V_{GS}=10V, T_C=25°C	*a	I_D	120	A
Continuous Drain Current @ V_{GS}=10V, T_C=100°C	*a		76	
Continuous Drain Current @ V_{GS}=10V, T_A=25°C	*b		24	
Continuous Drain Current @ V_{GS}=10V, T_A=70°C	*b		19	
Pulsed Drain Current	*c	I_{DM}	480	
Continuous Body Diode Forward Current @ T_C=25°C	*a	I_S	86	
Avalanche Current @ L=0.1mH		I_{AS}	40	
Avalanche Energy @ L=0.5mH		E_{AS}	100	mJ
Total Power Dissipation	T_C=25°C *a	P_D	104	W
	T_C=100°C *a		42	
	T_A=25°C *b		4.2	
	T_A=70°C *b		2.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	°C

Thermal Data

Parameter		Symbol	Steady State	Unit
Thermal Resistance, Junction-to-case		$R_{\theta JC}$	1.2	°C/W
Thermal Resistance, Junction-to-ambient	*b	$R_{\theta JA}$	30	

Note:

*a. The power dissipation P_D is based on $T_{J(MAX)}$=150℃, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

*b. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR -4 board with 2 oz. copper, in a still air environment with T_A=25℃. The power dissipation P_D is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150℃. The value in any given application depends on the user's specific board design.

*c. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃. Ratings are based on low frequency and low duty cycles to keep initial T_J=25℃.

Electrical Characteristics (T_A=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	100	-	-	V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	2	-	4		V_{DS}=V_{GS}, I_D=250μA
G_{FS}	-	43	-	S	V_{DS}=5V, I_D=20A
I_{GSS}	-	-	±100	nA	V_{GS}=±20V, V_{DS}=0V
I_{DSS}	-	-	1	μA	V_{DS}=80V, V_{GS}=0V
$R_{DS(ON)}$	-	3.2	4	mΩ	V_{GS}=10V, I_D=20A
Dynamic					
Ciss	-	6200	-	pF	V_{DS}=50V, V_{GS}=0V, f=1MHz
Coss	-	860	-		
Crss	-	40	-		
Rg	-	0.9	-	Ω	f=1MHz
Qg *1, 2	-	90	-	nC	V_{DS}=50V, I_D=20A, V_{GS}=10V
Qgs *1, 2	-	30	-		
Qgd *1, 2	-	20	-		
$t_{d(ON)}$ *1, 2	-	42	-	ns	V_{DS}=50V, I_D=20A, V_{GS}=10V, R_{GS}=1.6Ω
tr *1, 2	-	25	-		
$t_{d(OFF)}$ *1, 2	-	75	-		
t_f *1, 2	-	20	-		
Source-Drain Diode					
V_{SD} *1	-	0.8	1.2	V	I_S=20A, V_{GS}=0V
trr	-	63	-	ns	I_F=20A, dI_F/dt=100A/μs
Qrr	-	135	-	nC	

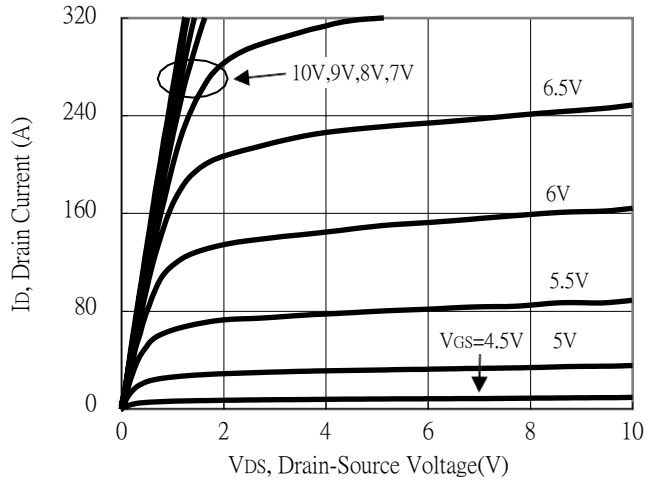
Note:

*1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

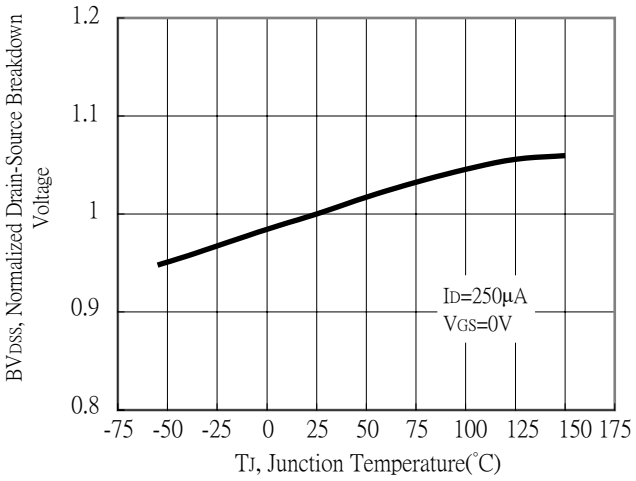
*2. Independent of operating temperature

Typical Characteristics

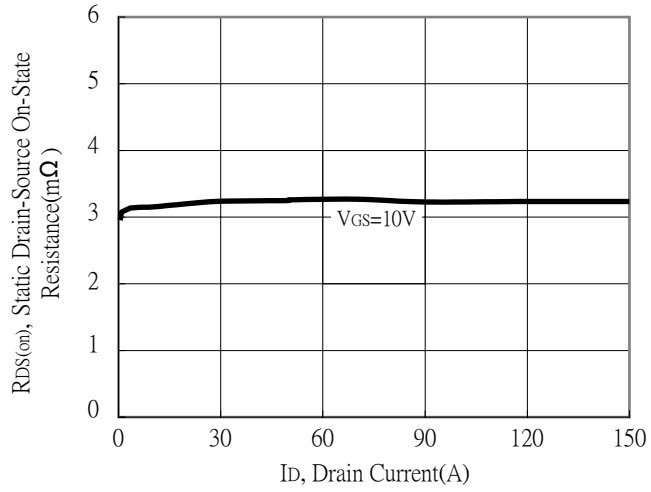
Typical Output Characteristics



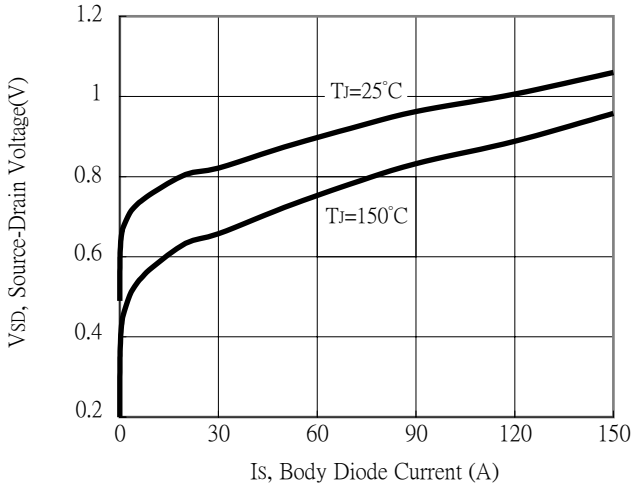
Breakdown Voltage vs Ambient Temperature



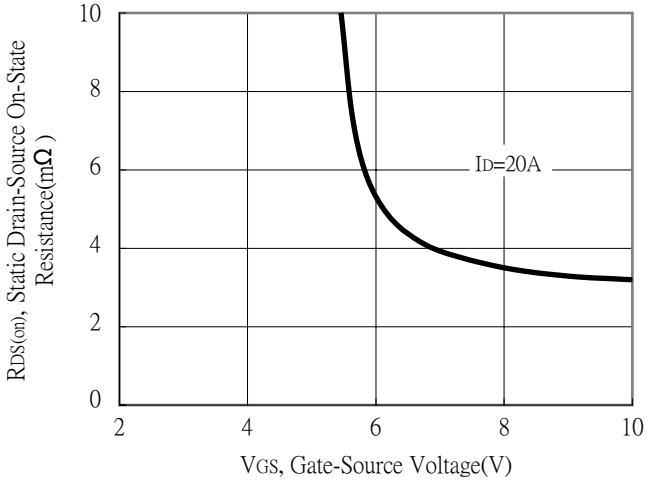
Static Drain-Source On-State resistance vs Drain Current



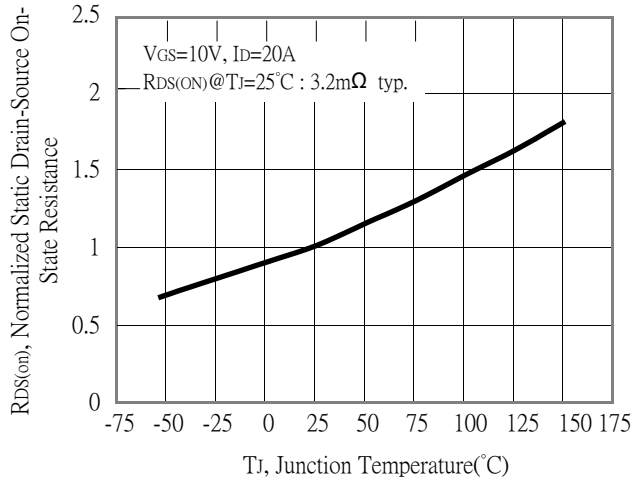
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

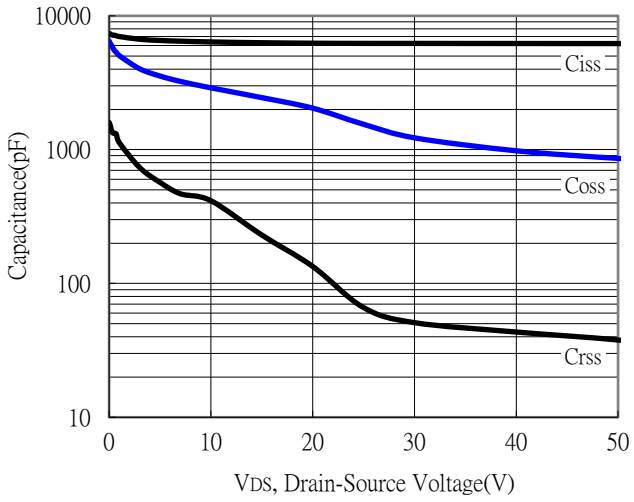


Drain-Source On-State Resistance vs Junction Temperature

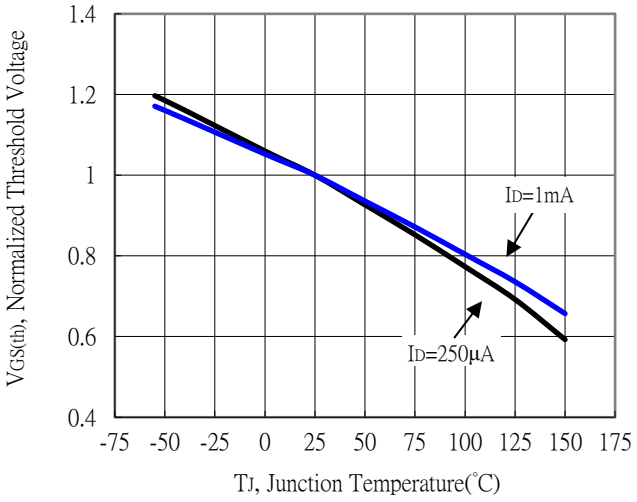


Typical Characteristics (Cont.)

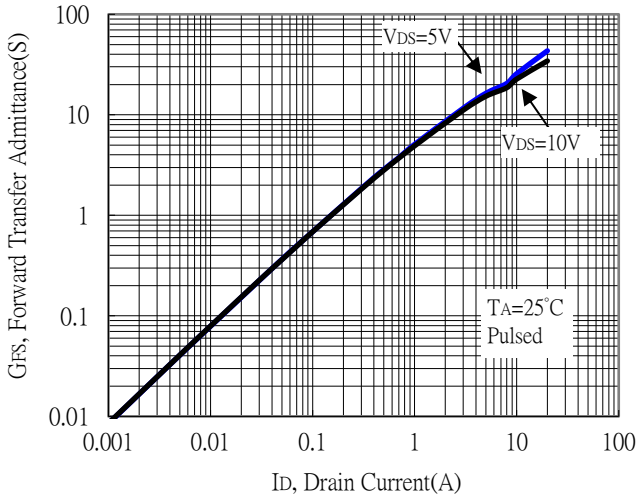
Capacitance vs Drain-to-Source Voltage



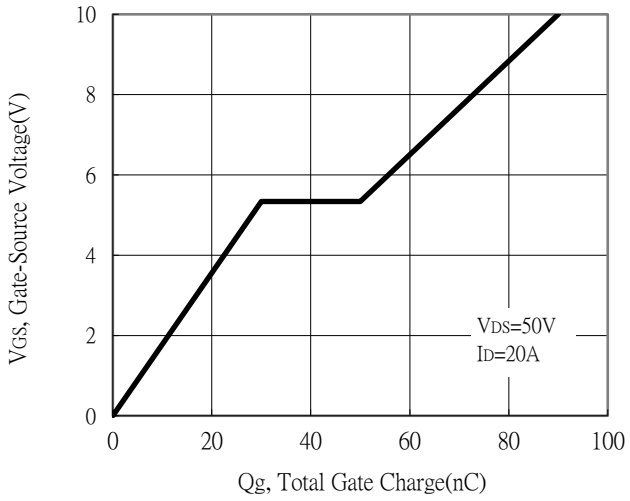
Threshold Voltage vs Junction Temperature



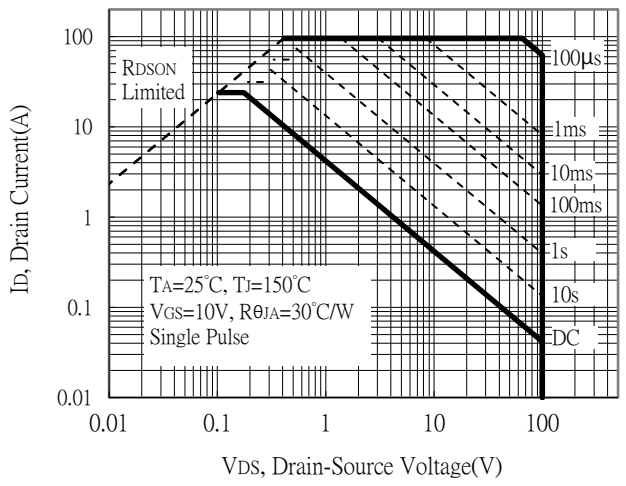
Forward Transfer Admittance vs Drain Current



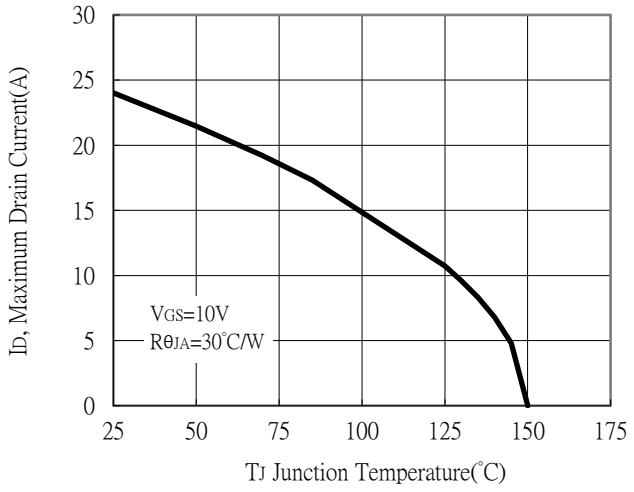
Gate Charge Characteristics



Maximum Safe Operating Area

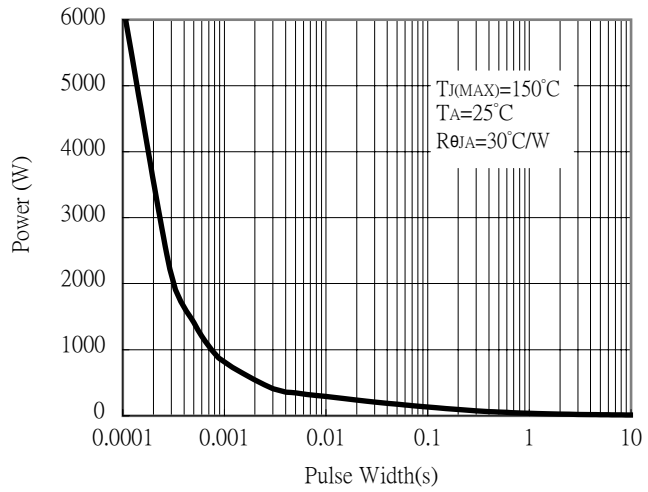


Maximum Drain Current vs Junction Temperature

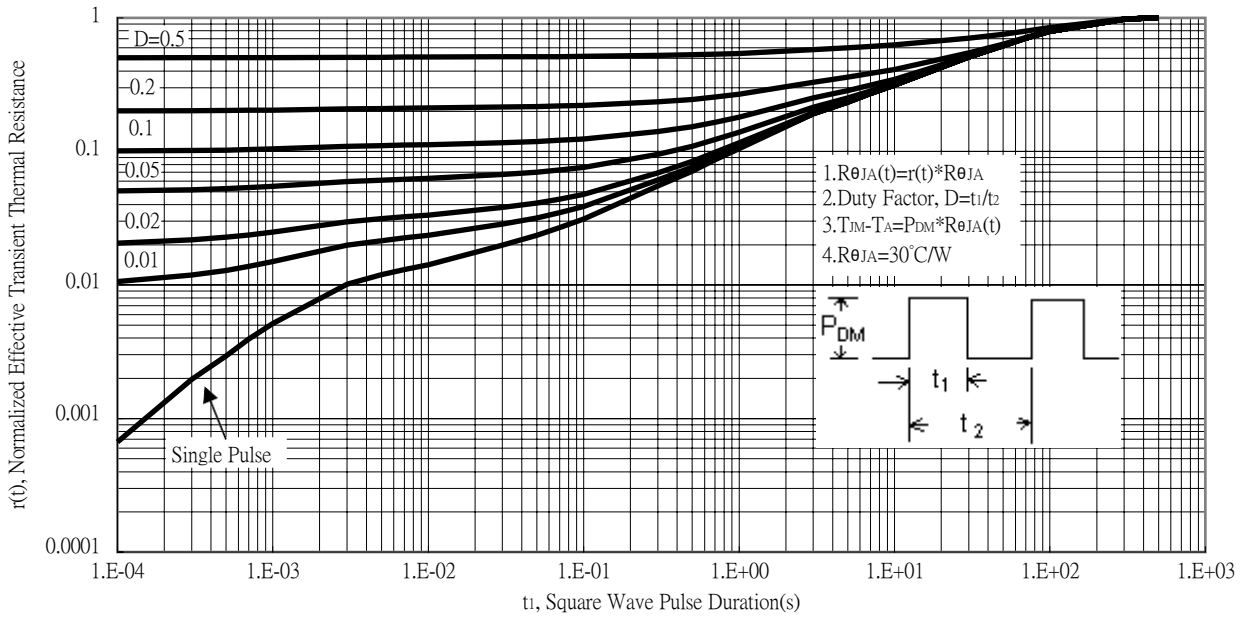


Typical Characteristics (Cont.)

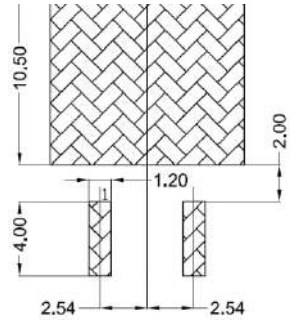
Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves

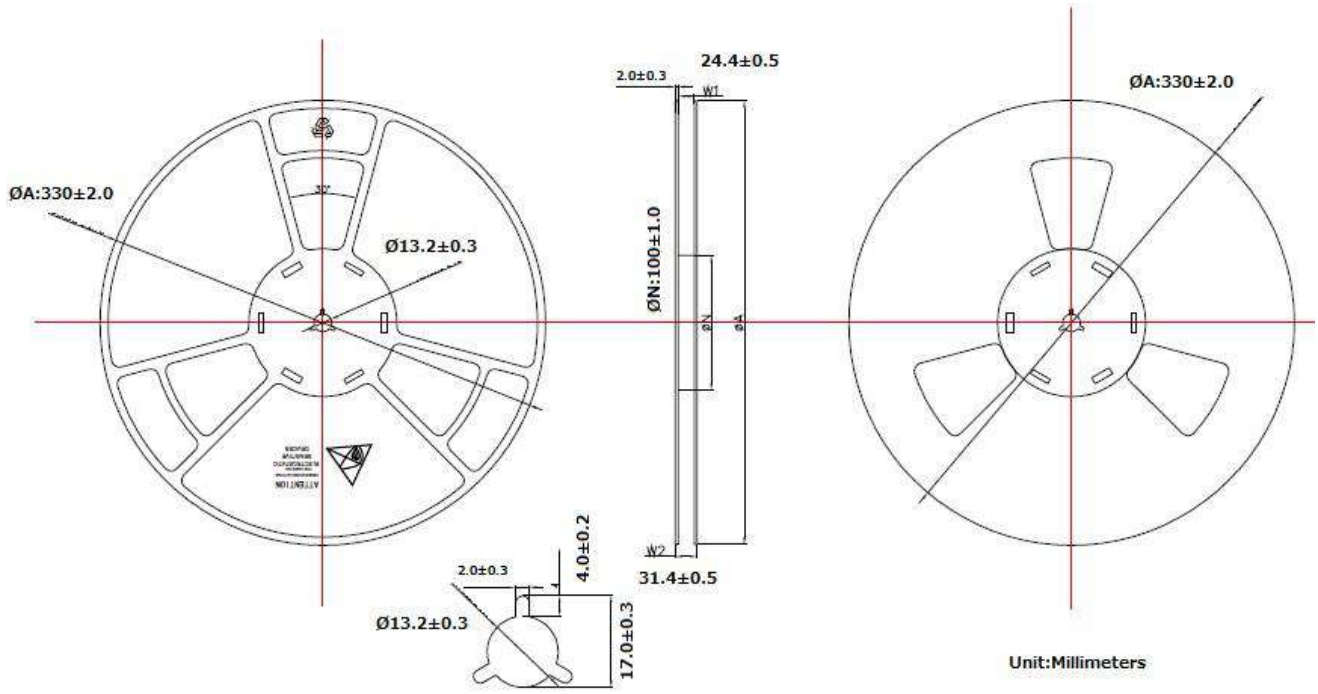


Recommended Soldering Footprint

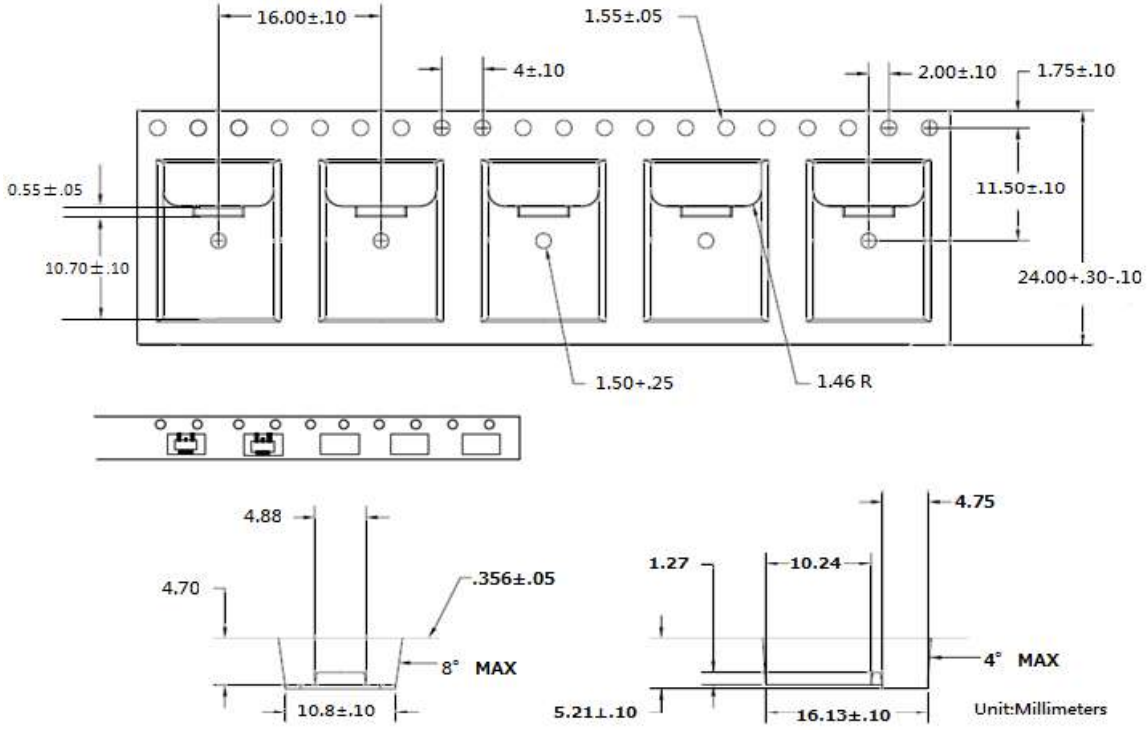


Unit:mm

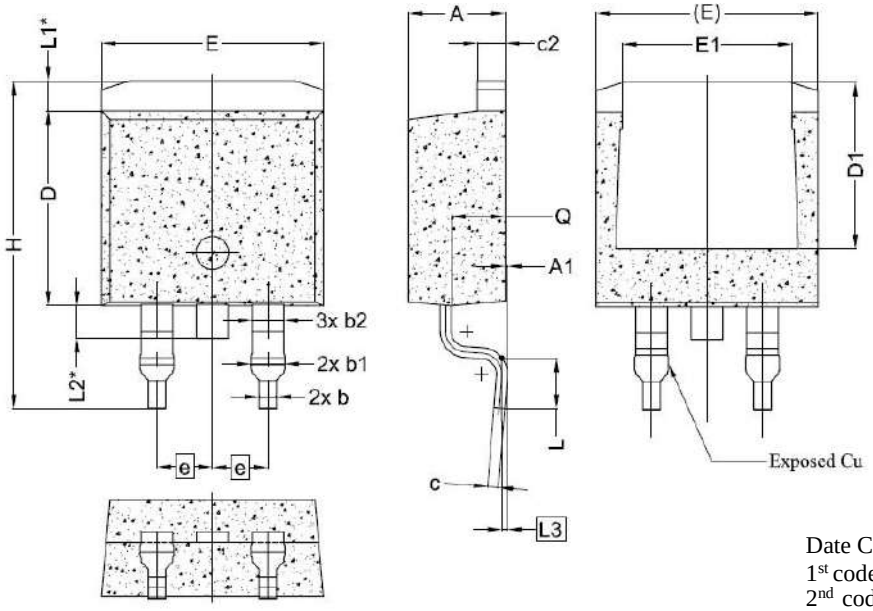
Reel Dimension



Carrier Tape Dimension

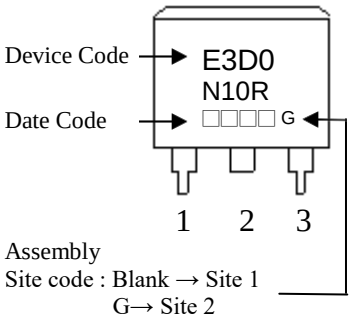


TO-263 Dimension



3-Lead Plastic Surface Mounted Package

Marking :



Assembly
Site code : Blank → Site 1
G→ Site 2

Style : Pin 1.Gate 2.Drain
3.Source

Date Code(counting from left to right) :
1st code: year code, the last digit of Christian year
2nd code : month code, Jan→A, Feb→B, Mar→C,
Apr→D, May→E, Jun→F, Jul→G, Aug→H,
Sep→J, Oct→K, Nov→L, Dec→M
3rd and 4th codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.24	4.64	0.166	0.182	E	9.96	10.36	0.392	0.407
A1	0.00	0.25	0.000	0.009	E1	6.89	7.89	0.271	0.310
b	0.70	0.90	0.027	0.035	e	2.54 BSC		0.100 BSC	
b1	1.20	1.75	0.047	0.068	H	14.61	15.88	0.575	0.625
b2	1.20	1.70	0.047	0.066	L	1.78	2.79	0.070	0.109
c	0.40	0.60	0.015	0.023	L1	1.36 REF		0.053 REF	
c2	1.15	1.40	0.045	0.055	L2	1.50 REF		0.059 REF	
D	8.82	9.02	0.347	0.355	L3	0.25 BSC		0.009 BSC	
D1	6.86	-	0.27	-	Q	2.30	2.70	0.090	0.106